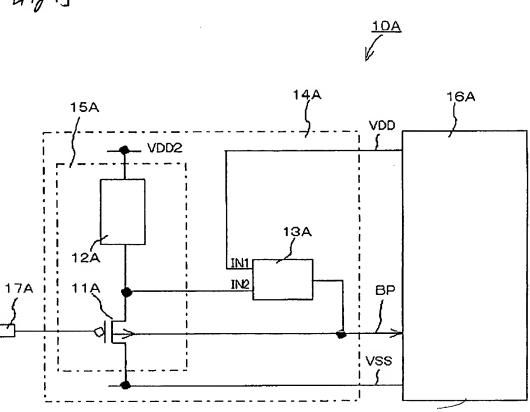
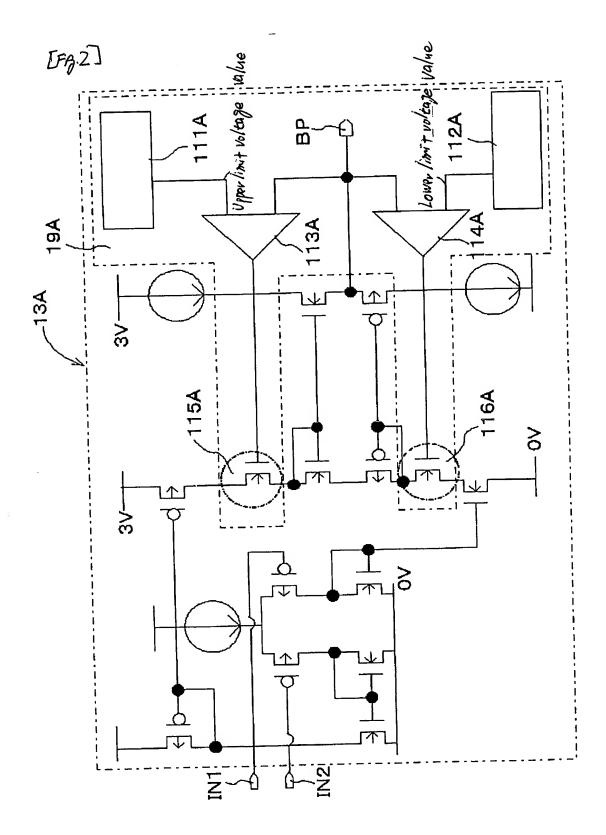
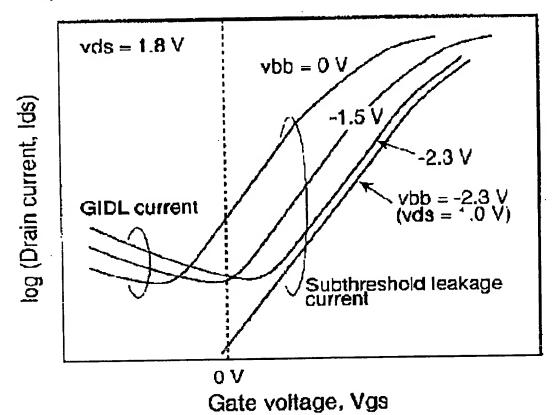
[Fig. 1]







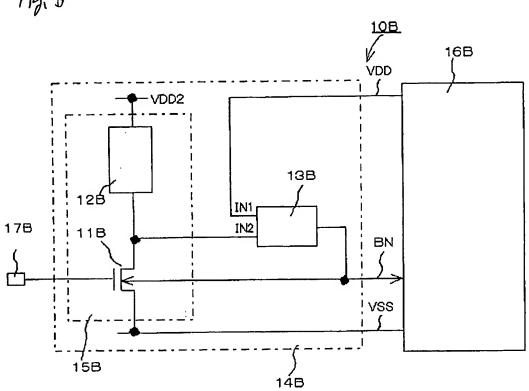
[Fig.4]

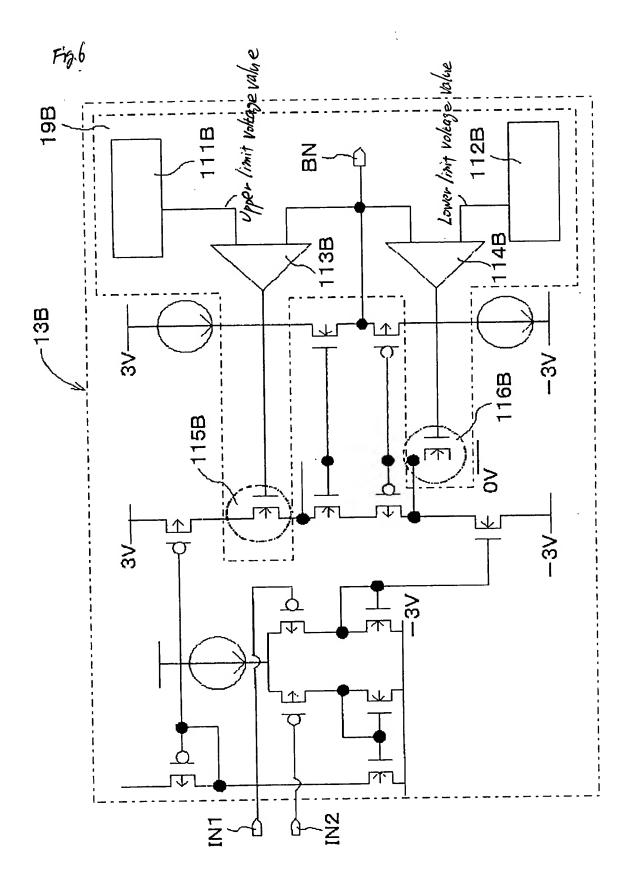
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-2 -1 0 1 2

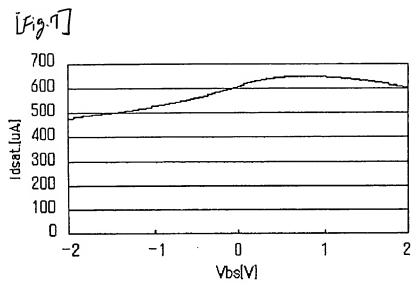
Vbs[V]

Ids-Vbs characteristics of p-type Mosfet

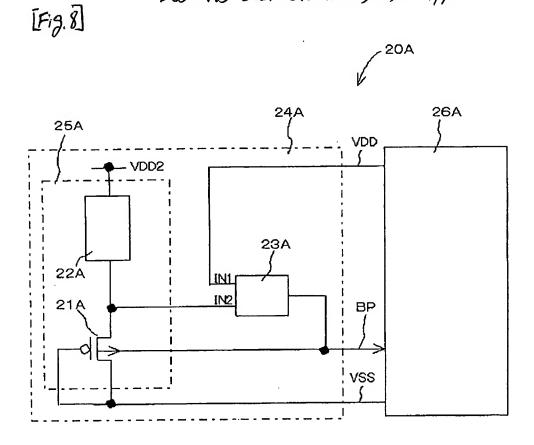
Fig. 5

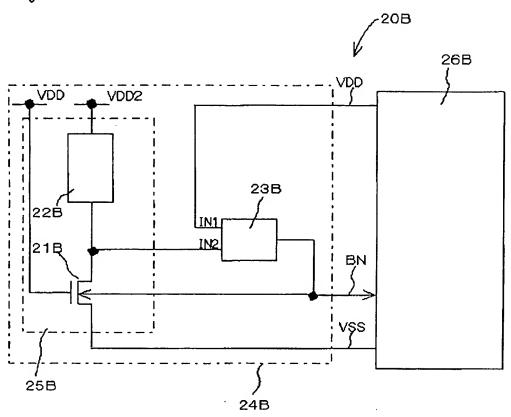


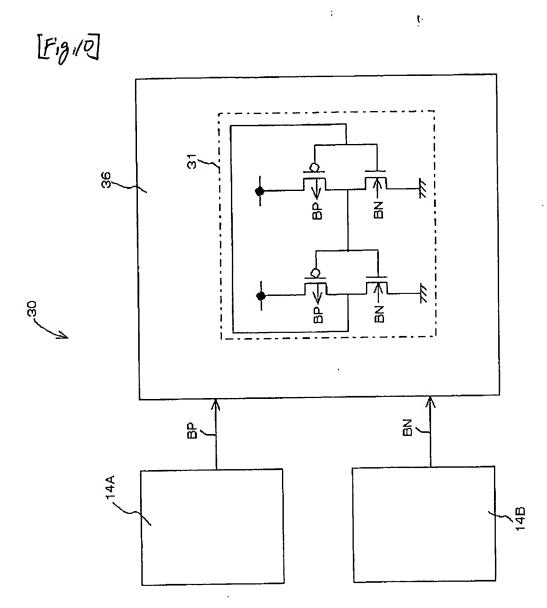


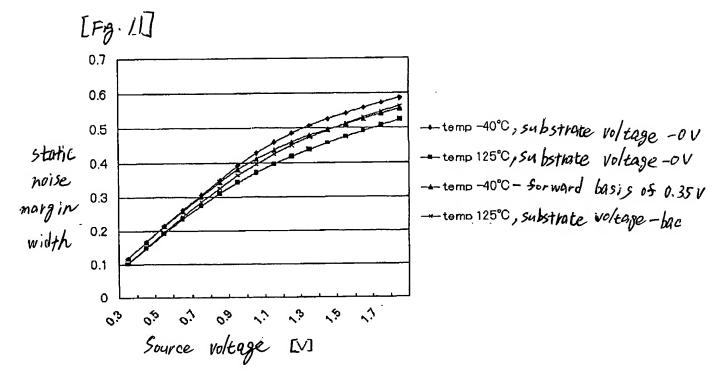


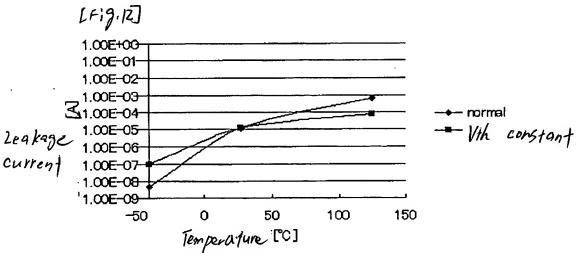
Ids-Vbs characteristics of n-type Mos FET



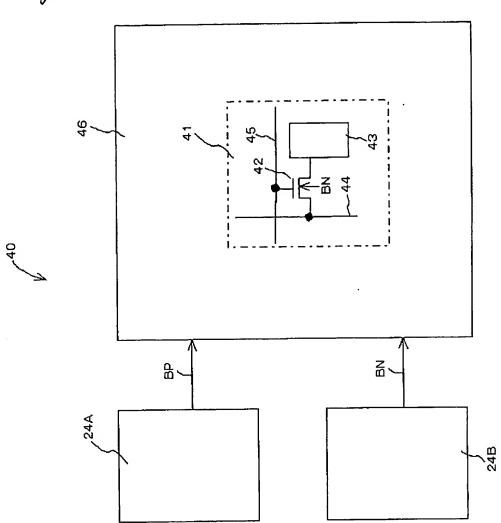




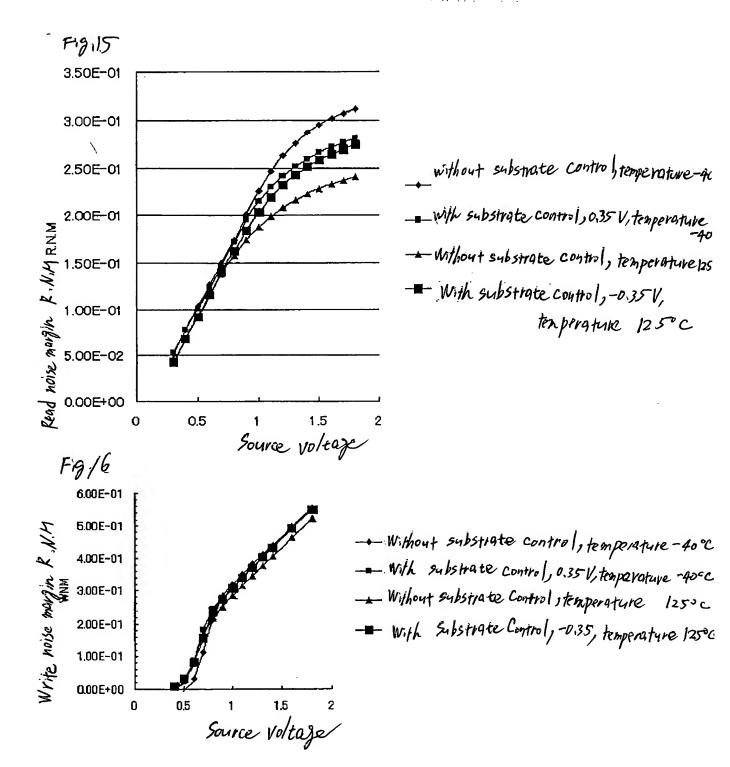


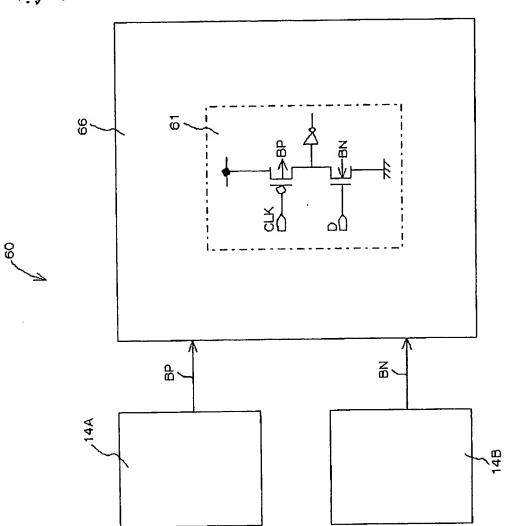


[F.g.13]



F17.14. -<u>S</u> ABP Na L 9, 5, Na Na 50 윱, M. ,14A 14B





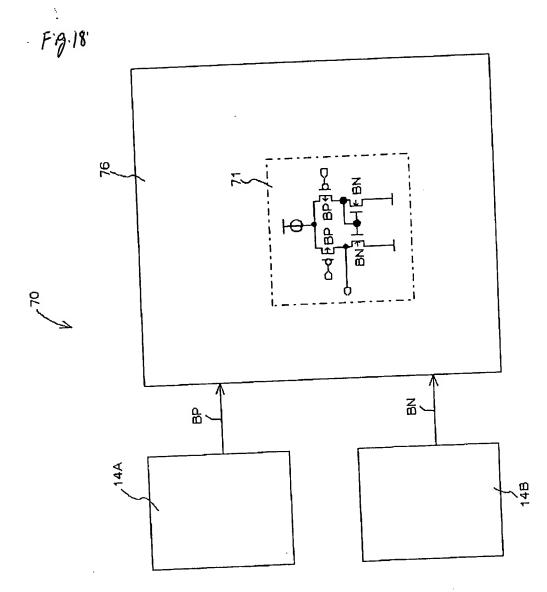
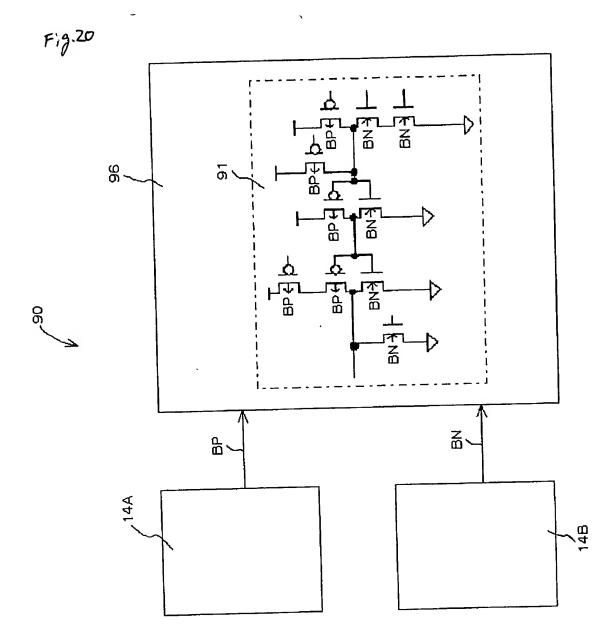
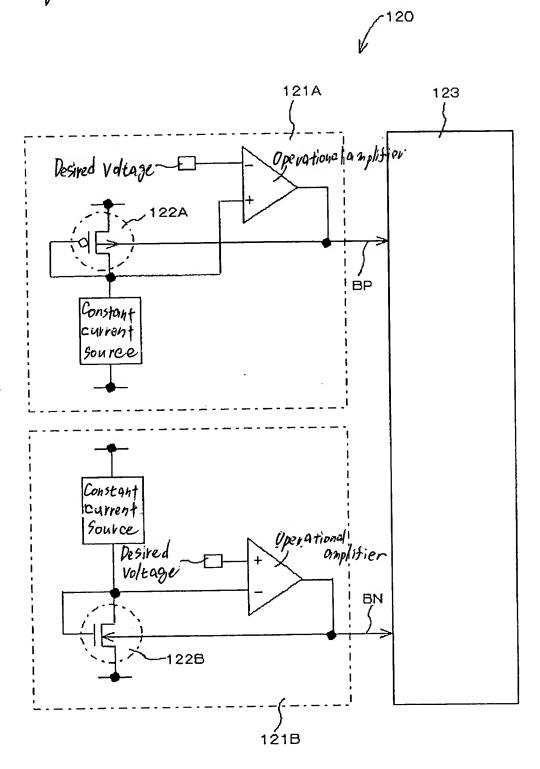
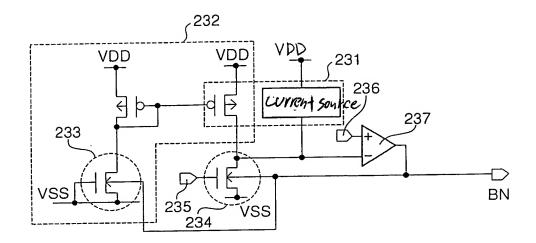


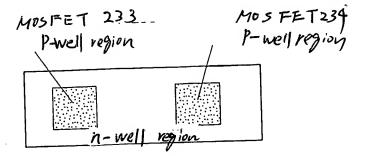
Fig./91ит. ит. 80 80 N N 96 8 S. g, 14A 14B

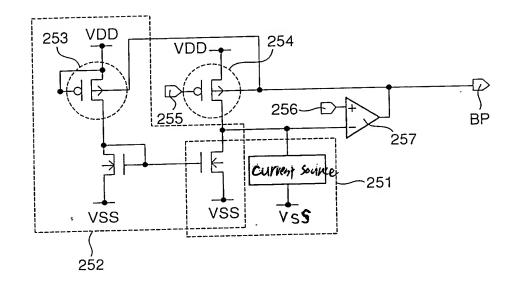


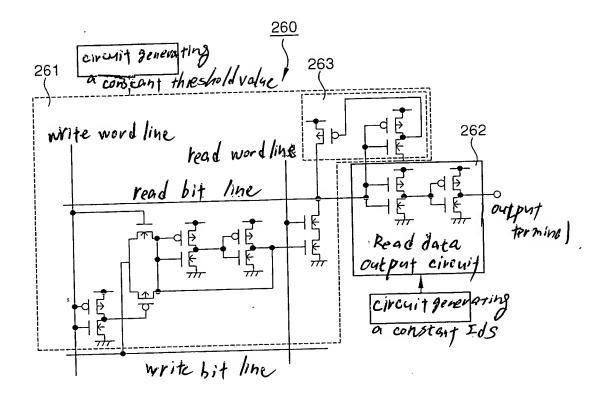
[Fig. 2] 106 100 S. д,

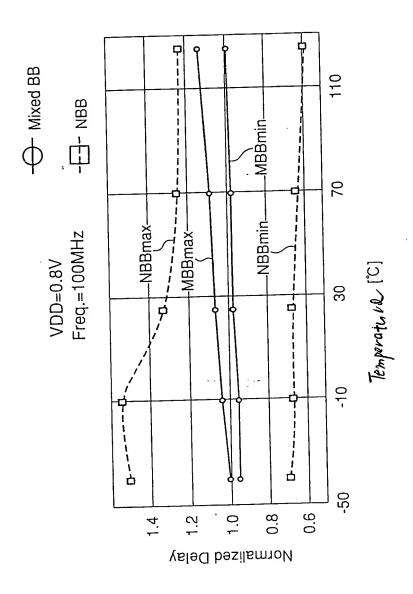


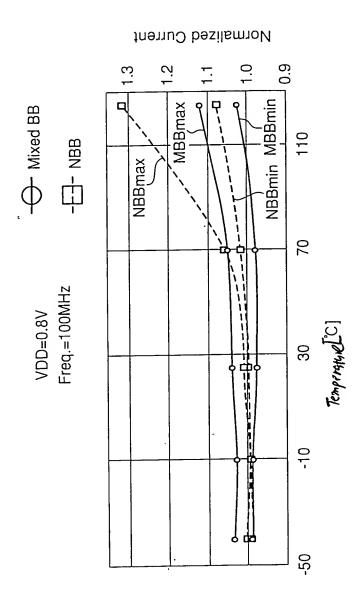


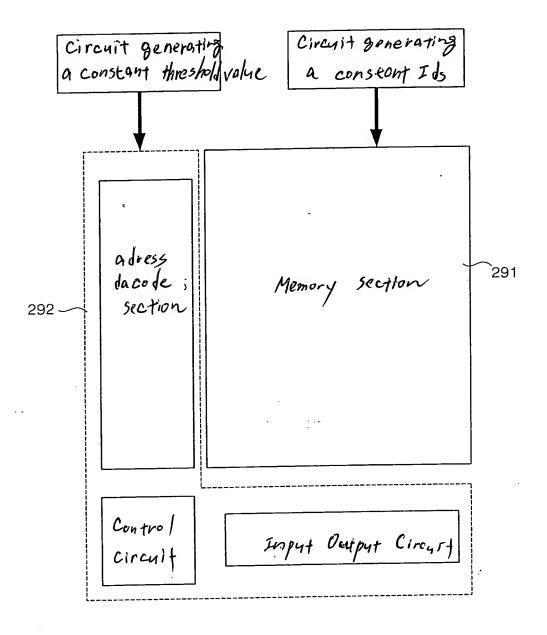


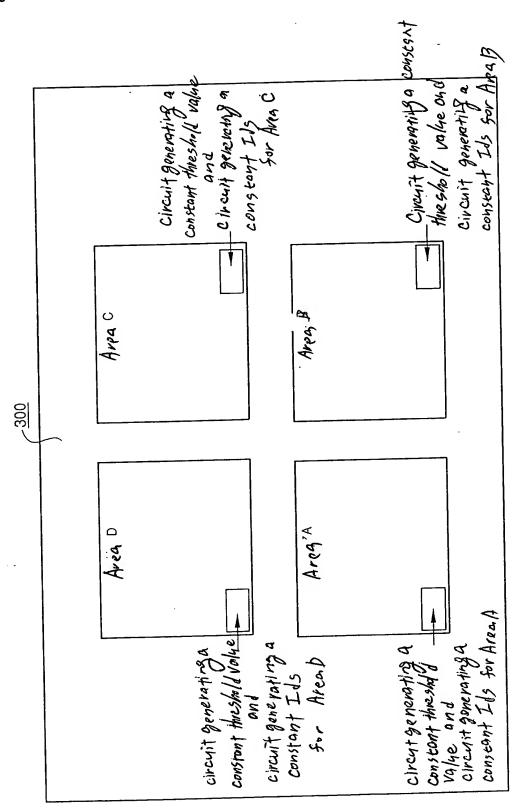


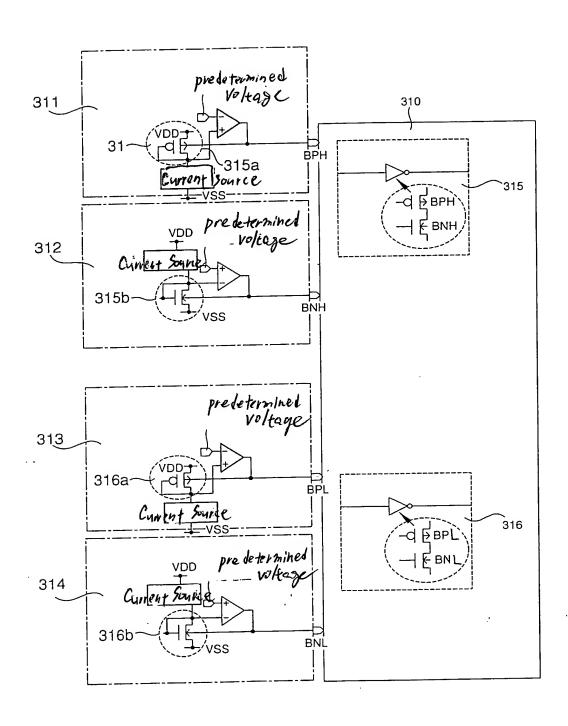


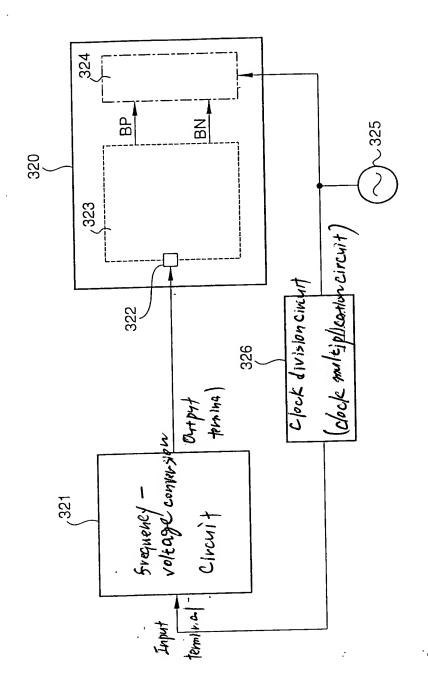


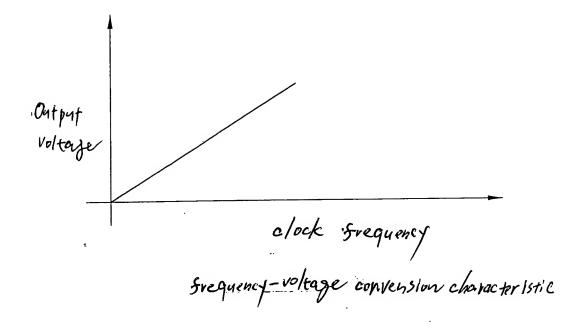




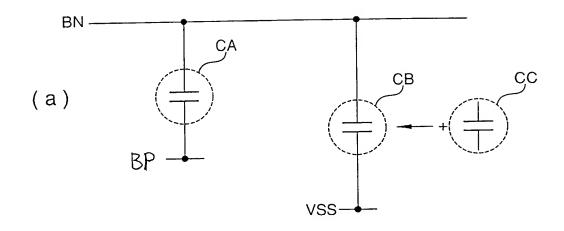


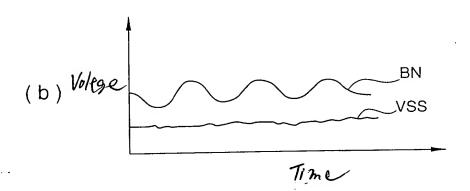


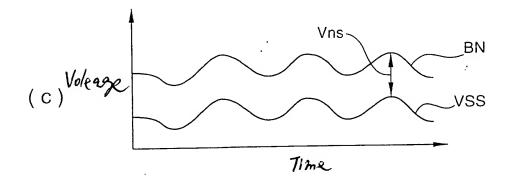




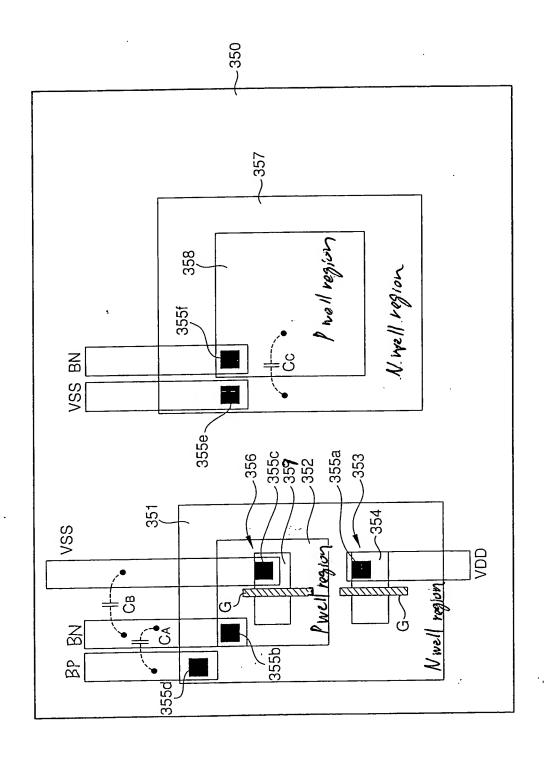
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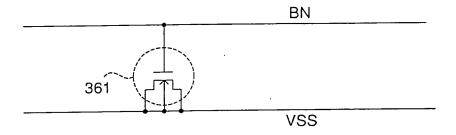


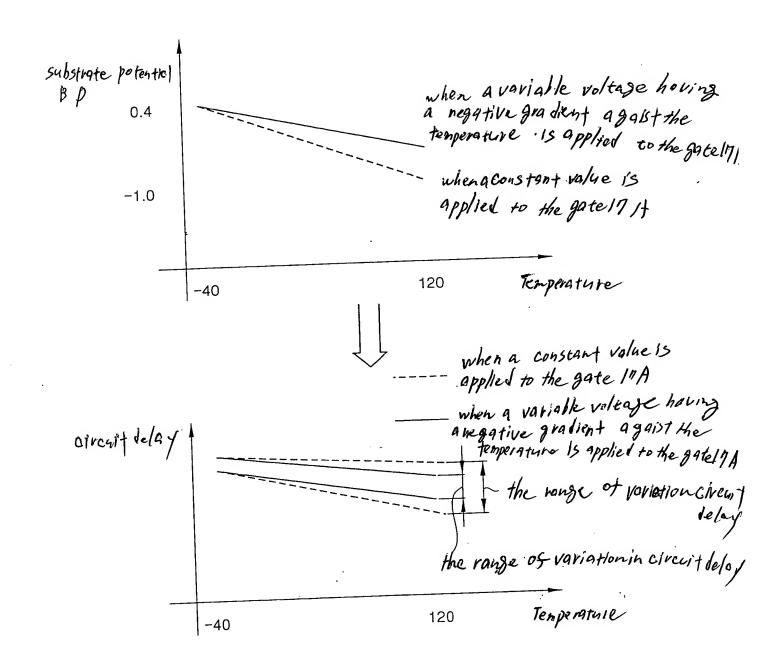




F19.35







-[Fig.38]

